

PCN Number:	20150505003A		PCN Date:	07/25/2016																			
Title:	Add Cu as Alternative Wire Base Metal for Selected Device(s)																						
Customer Contact:	PCN Manager	Dept:	Quality Services																				
Proposed 1st Ship Date:	08/14/2015		Estimated Sample Availability:	Date provided at sample request																			
Change Type:																							
<input type="checkbox"/>	Assembly Site	<input type="checkbox"/>	Design	<input type="checkbox"/>	Wafer Bump Site																		
<input checked="" type="checkbox"/>	Assembly Process	<input type="checkbox"/>	Data Sheet	<input type="checkbox"/>	Wafer Bump Material																		
<input checked="" type="checkbox"/>	Assembly Materials	<input type="checkbox"/>	Part number change	<input type="checkbox"/>	Wafer Bump Process																		
<input type="checkbox"/>	Mechanical Specification	<input type="checkbox"/>	Test Site	<input type="checkbox"/>	Wafer Fab Site																		
<input type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process	<input type="checkbox"/>	Wafer Fab Materials																		
				<input type="checkbox"/>	Wafer Fab Process																		
PCN Details																							
Description of Change:																							
<p>Revision A is to announce the <u>retraction</u> of select devices. These devices will continue to be manufactured as prior and will not be subjected to the change described in this notification. Affected devices are identified above in Pg 2.</p> <p>Texas Instruments is pleased to announce the qualification of Cu as an additional bond wire option for devices listed in "Product affected" section below. Devices will remain in current assembly facilities and there will be no other piece part changes:</p>																							
<table border="1"> <thead> <tr> <th>Pkg Family</th> <th>Current Wire</th> <th>Additional Wire</th> </tr> </thead> <tbody> <tr> <td>SOT23</td> <td>Au, 1.0 mil</td> <td>Cu, 0.96 mil</td> </tr> <tr> <td>SOIC</td> <td>Au, 1.0 mil</td> <td>Cu, 0.96 mil</td> </tr> <tr> <td>VSSOP</td> <td>Au, 1.0 mil</td> <td>Cu, 0.96 mil</td> </tr> <tr> <td>TSSOP</td> <td>Au, 1.0 mil</td> <td>Cu, 0.96 mil</td> </tr> <tr> <td>QFN</td> <td>Au, 1.0 mil</td> <td>Cu, 0.80 mil</td> </tr> </tbody> </table>						Pkg Family	Current Wire	Additional Wire	SOT23	Au, 1.0 mil	Cu, 0.96 mil	SOIC	Au, 1.0 mil	Cu, 0.96 mil	VSSOP	Au, 1.0 mil	Cu, 0.96 mil	TSSOP	Au, 1.0 mil	Cu, 0.96 mil	QFN	Au, 1.0 mil	Cu, 0.80 mil
Pkg Family	Current Wire	Additional Wire																					
SOT23	Au, 1.0 mil	Cu, 0.96 mil																					
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TSSOP	Au, 1.0 mil	Cu, 0.96 mil																					
QFN	Au, 1.0 mil	Cu, 0.80 mil																					
Reason for Change:																							
<p>Continuity of supply.</p> <ol style="list-style-type: none"> 1) To align with world technology trends and use wiring with enhanced mechanical and electrical properties 2) Maximize flexibility within our Assembly/Test production sites. 3) Cu is easier to obtain and stock 																							
Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):																							
None																							
Changes to product identification resulting from this PCN:																							
None																							
Product Affected:																							
See Page 2.																							

Qualification Report

0.96 mil Cu wire qual for SOT23 Packages

Product Attributes

Attributes	Qual Device: LM4041AIM3-1.2	Qual Device: LP3985IM5X-5.0	Qual Device: LMC7101AIM5NOPB	Qual Device: LM431CCM3NOPB
Assembly Site	TIEMA	TIEMA	TIEMA	TIEMA
Package Family	SOT	SOT	SOT	SOT
Flammability Rating	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0
Wafer Fab Supplier	GFAB	MFAB	GFAB	GFAB
Wafer Fab Process	BPLFAST-1	CMOS7	P2CMOS	SLM

Qualification Results

*Data Displayed as: Number of lots / Total sample size /
Total failed*

Type	Test Name / Condition	Duration	Qual Device: LM4041AIM3-1.2	Qual Device: LP3985IM5X-5.0	Qual Device: LMC7101AIM5NOPB	Qual Device: LM431CCM3NOPB
PC	PreCon Level 1	Level 1- 260C	3/693/0	3/462/0	3/693/0	3/462/0
HAST	Biased HAST, 130C/85%RH	96/hrs. @130C	3/231/0	-	3/231/0	-
AC	Autoclave 121C	96HRS	3/231/0	3/231/0	3/231/0	3/231/0
TC	Temperature Cycle, -65/150C	TMCL500X	3/231/0	3/231/0	3/231/0	3/231/0
HTSL	High Temp Storage Bake 150C	1000 hrs. @150C	1/77/0	-	1/77/0	1/77/0
MQ	Manufacturability (Assembly)	(per mfg. Site specification)	Pass	Pass	Pass	Pass
DPA	Destructive Physical Analysis Post 500 Temp Cycle	x-section and de process to examine assembly robustness, Check for stich bond and bond pad integrity	3/15/0	3/15/0	3/15/0	3/15/0
YLD	FTY and Bin Summary	Compare against baseline	Pass	Pass	Pass	Pass

Qualification Report

0.96 mil Cu wire qual for SOIC Packages

Product Attributes

Attributes	Qual Device: DS90CP22MXA1CL	Qual Device: LMV324MX	Qual Device: LP2995MXNOPB	Qual Device: LMC6482AIM/NOPB
Assembly Site	TIEMA	TIEMA	TIEMA	TIEMA
Package Family	SOIC	SOIC	SOIC	SOIC
Flammability Rating	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0
Wafer Fab Supplier	MFAB	MFAB	MFAB	GFAB
Wafer Fab Process	CMOS7	CS80	CS65	P2CMOS

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	Test Name / Condition	Duration	Qual Device: DS90CP22MXA1CL	Qual Device: LMV324MX	Qual Device: LP2995MXNOPB	Qual Device: LMC6482AIM/NOPB
PC	PreCon Level 1	Level 1-260C	3/462/0	-	3/462/0	3/693/0
HAST	Biased HAST, 130C/85%RH	96/hrs. @ 130C	-	-	-	3/231/0
AC	Autoclave 121C	96HRS	3/231/0	-	3/231/0	3/231/0
TC	Temperature Cycle, -65/150C	TMCL500X	3/231/0	-	3/231/0	3/231/0
HTSL	High Temp Storage Bake 150C	1000 hrs. @ 150C	-	-	-	1/77/0
MQ	Manufacturability (Assembly)	(per mfg. Site specification)	-	Pass	Pass	Pass
DPA	Destructive Physical Analysis Post 500 Temp Cycle	x-section and de process to examine assembly robustness, Check for stich bond and bond pad integrity	3/15/0	-	3/15/0	3/15/0
YLD	FTY and Bin Summary	Compare against baseline	-	Pass	Pass	Pass

Qualification Report

0.96 mil Cu wire qual for VSSOP & TSSOP Packages

Product Attributes

Attributes	Qual Device: LMV852MMX	Qual Device: LMC6482IMM	Qual Device: LM93CIMT	Qual Device: LM5642MHX
Assembly Site	TIEMA	TIEMA	TIEMA	TIEMA
Package Family	VSSOP	VSSOP	TSSOP	TSSOP
Flammability Rating	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0
Wafer Fab Supplier	MFAB	GFAB	MFAB	MFAB
Wafer Fab Process	CMOS7	P2CMOS	CMOS7	ABCD150

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	Test Name / Condition	Duration	Qual Device: LMV852MMX	Qual Device: LMC6482IMM	Qual Device: LM93CIMT	Qual Device: LM5642MHX
PC	PreCon Level 1	Level 1-260C	3/462/0	3/462/0	-	3/231/0
PC	PreCon Level 2	Level 2-260C	-	-	3/693/0	-
HAST	Biased HAST, 130C/85%RH	96/hrs. @130C	-	-	3/231/0	-
AC	Autoclave 121C	96HRS	3/231/0	3/231/0	3/231/0	-
TC	Temperature Cycle, -65/150C	TMCL500X	3/231/0	3/231/0	3/231/0	3/231/0
HTSL	High Temp Storage Bake 150C	1000 hrs. @150C	-	-	1/77/0	-
MQ	Manufacturability (Assembly)	(per mfg. Site specification)	Pass	Pass	-	-
DPA	Destructive Physical Analysis Post 500 Temp Cycle	x-section and de process to examine assembly robustness, Check for stich bond and bond pad integrity	3/15/0	3/15/0	-	3/15/0
YLD	FTY and Bin Summary	Compare against baseline	Pass	Pass	-	-

Qualification Report

0.96 mil Cu wire qual for TSSOP Packages

Product Attributes

Attributes	Qual Device: LMH0346MH	Qual Device: LM5037MT	Qual Device: LM3657MH/NOPB	Qual Device: SCANSTA111MTX
Assembly Site	TIEMA	TIEMA	TIEMA	TIEMA
Package Family	TSSOP	TSSOP	TSSOP	TSSOP
Flammability Rating	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0
Wafer Fab Supplier	MFAB	GFAB	MFAB	MFAB
Wafer Fab Process	BICMOS8B+	ABCD150	CMOS7	CMOS7

Qualification Results

*Data Displayed as: Number of lots / Total sample size /
Total failed*

Type	Test Name / Condition	Duration	Qual Device: LMH0346MH	Qual Device: LM5037MT	Qual Device: LM3657MH/NOPB	Qual Device: SCANSTA111MTX
PC	PreCon Level 1	Level 1- 260C	-	3/693/0	3/462/0	-
PC	PreCon Level 2	Level 2- 260C	-	-	-	3/462/0
PC	PreCon Level 3	Level 3- 260C	3/231/0	-	-	-
THBT	THBT 85C, 85%RH	1000/hrs. @85C	-	3/231/0	-	-
AC	Autoclave 121C	96HRS	-	3/231/0	3/231/0	3/231/0
TC	Temperature Cycle, -65/150C	TMCL500X	3/231/0	3/231/0	3/231/0	3/231/0
HTSL	High Temp Storage Bake 150C	1000 hrs. @150C	-	1/77/0	-	-
MQ	Manufacturability (Assembly)	(per mfg. Site specification)	Pass	Pass	Pass	Pass
DPA	Destructive Physical Analysis Post 500 Temp Cycle	x-section and de process to examine assembly robustness, Check for stich bond and bond pad integrity	3/15/0	3/15/0	3/15/0	3/15/0
YLD	FTY and Bin Summary	Compare against baseline	Pass	Pass	Pass	Pass

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

Qualification Report

0.8 mils Cu wire qual on BC13, CMOS9T and CMOS7 in WQFN and WSON Packages

Approved 09/23/2014

Product Attributes

Attributes	Qual Device: DP83848T SQ	Qual Device: DS91M040TSQ AW2	Qual Device: DS100DX410EL 16	Qual Device: DS80PCI402A2TT	Qual Device: LMH0366SQENOPB	Qual Device: LMH0394SQ/NOPB
Assembly Site	TIEM-AT	TIEM-AT	TIEM-AT	TIEM-AT	TIEM-AT	TIEM-AT
Package Family	WQFN	WQFN	WQFN	WQFN	WQFN	QFN
Flammability Rating	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0
Wafer Fab Supplier	MAINEFAB	MAINEFAB	MAINEFAB	MAINEFAB	MAINEFAB	MAINEFAB
Wafer Fab Process	CMOS9T	CMOS7	BICMOS13	BICMOS13	BICMOS13	BICMOS13

- QBS: Qual By Similarity
- Qual Device DS100DX410EL16 is qualified at LEVEL3-260C
- Qual Device DS80PCI402A2TT is qualified at LEVEL2-260C
- Qual Device LMH0366SQENOPB is qualified at LEVEL1-260C
- Qual Device LMH0394SQ/NOPB is qualified at -
- Qual Device LMH0394SQ/NOPB REV A is qualified at LEVEL3-260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	Test Name / Condition	Duration	Qual Device: DP83848T SQ	Qual Device: DS91M040TSQ AW	Qual Device: DS100DX410 EL16	Qual Device: DS80PCI402 A2TT	Qual Device: LMH0366SQEN OPB	Qual Device: LMH0394SQ/N OPB
PC	PreCon Level 1	Level 1-260C					3/720/0	
PC	PreCon Level 2	Level 2-260C	3/1079/0		-	3/720/0	-	-
PC	PreCon Level 3	Level 3-260C	-	1/255/0	3/720/0	-	-	3/231/0
HAST	Biased HAST, 130C/85%RH	96/hrs. @130C	-	-	-	-	-	3/231/0
AC	Autoclave 121C	96HRS	3/231/0	1/77/0	3/231/0	3/231/0	3/231/0	-
UHAST	Unbiased HAST 130C/85%RH	unHAST-96 HRS/-H	3/231/0	1/77/0	3/231/0	3/231/0	3/231/0	-
TC	Temperature Cycle, -65/150C	TMCL500X	3/231/0	1/77/0	3/231/0	3/231/0	3/231/0	-
HTSL	High Temp Storage Bake 170C	420 hrs. @170C	3/231/0	-	-	3/231/0	-	-

ED	Side By Side Electrical Characterization.	Per Datasheet Parameters	1/30/0	1/30/0	1/30/0	1/30/0	1/30/0	-
MQ	Manufacturability (Assembly)	(per mfg. Site specification)	Pass	Pass	Pass	Pass	Pass	Pass
MSL	Thermal Path Integrity	Level 2-260C	3/30/0	1/22/0	3/66/0	3/66/0	3/66/0	-
DPA	Destructive Physical Analysis Post 500 Temp Cycle	x-section and de process to examine assembly robustness, Check for stich bond and bond pad integrity	3/3/0	-	3/15/0	3/15/0	3/15/0	1/5/0 Post 96 hours HAST
YLD	FTY and Bin Summary	Compare against baseline	Pass	Pass	Pass	Pass	Pass	Pass

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

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Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

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